

2SK1061

High Speed Switching Applications

Analog Switch Applications

Interface Applications

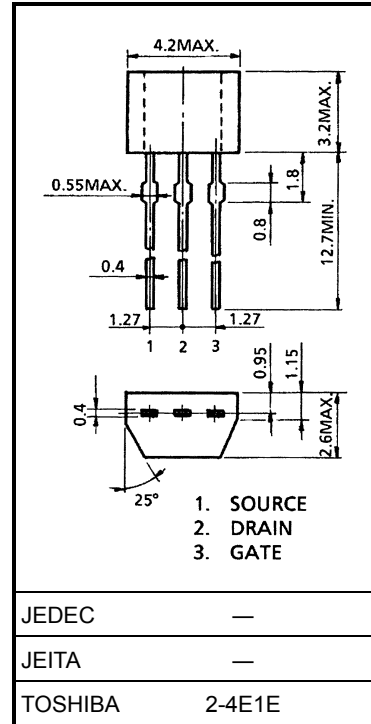
- Excellent switching times: $t_{on} = 14 \text{ ns}$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 100 \text{ mS}$ (min)
- Low on resistance: $R_{DS(ON)} = 0.6 \Omega$ (typ.)
- Enhancement-mode
- Complementary to 2SJ167

Absolute Maximum Ratings (Ta = 25°C)

| Characteristics | Symbol | Rating | Unit |
|-------------------------------------|-----------|----------|------|
| Drain-source voltage | V_{DS} | 60 | V |
| Gate-source voltage | V_{GSS} | ± 20 | V |
| Drain current | DC | I_D | 200 |
| | Pulse | I_{DP} | 800 |
| Drain power dissipation (Ta = 25°C) | P_D | 300 | mW |
| Channel temperature | T_{ch} | 150 | °C |
| Storage temperature range | T_{stg} | -55~150 | °C |

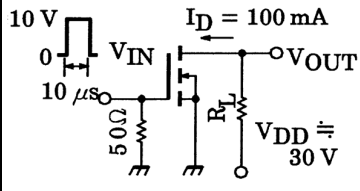
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Unit: mm

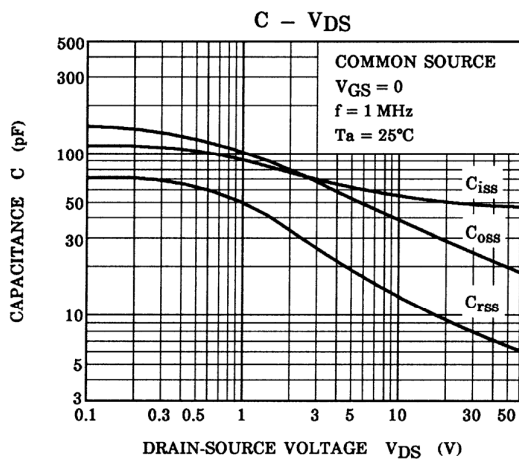
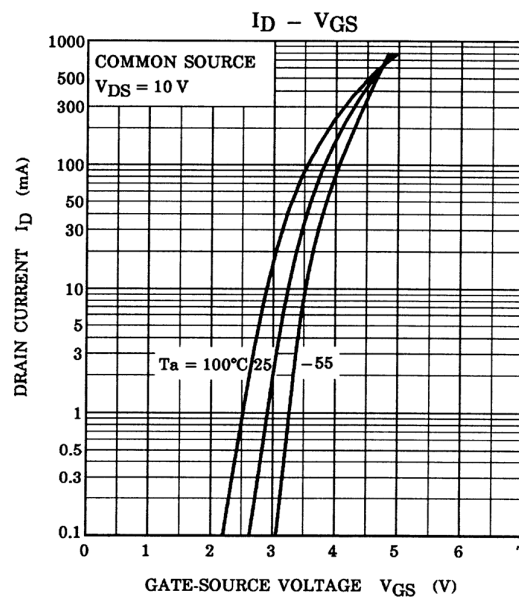
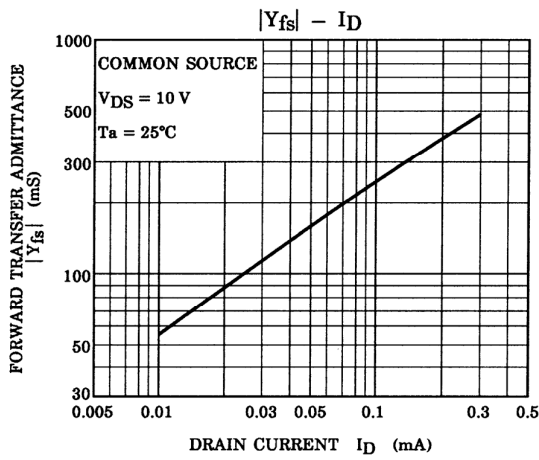
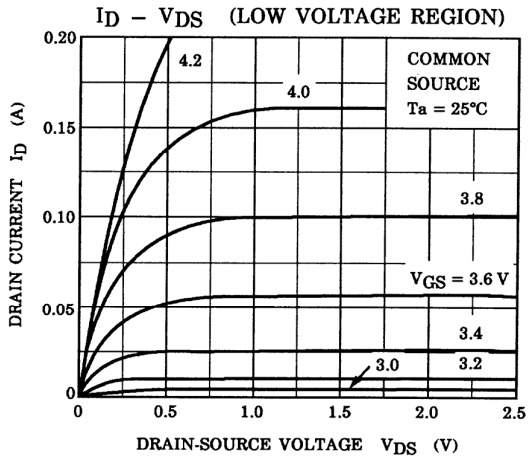
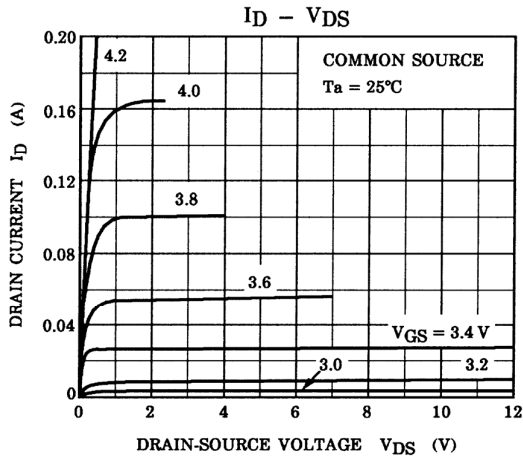


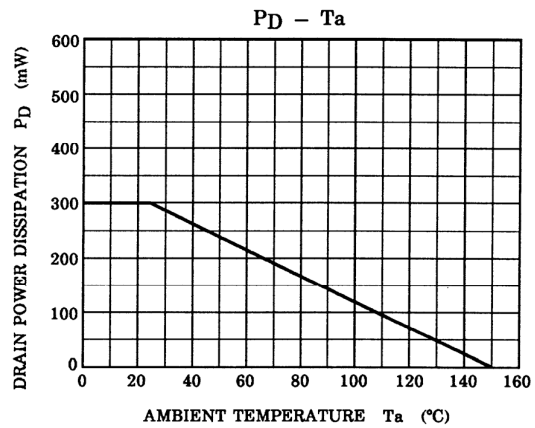
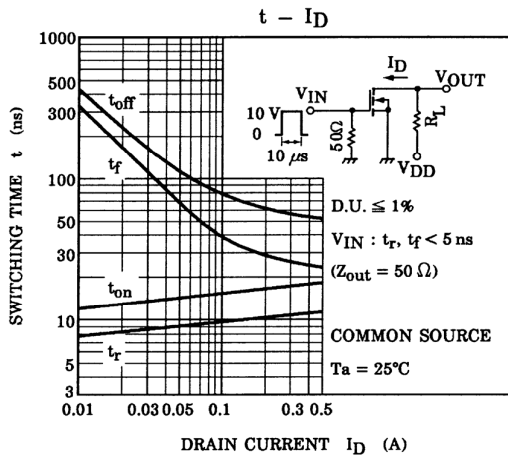
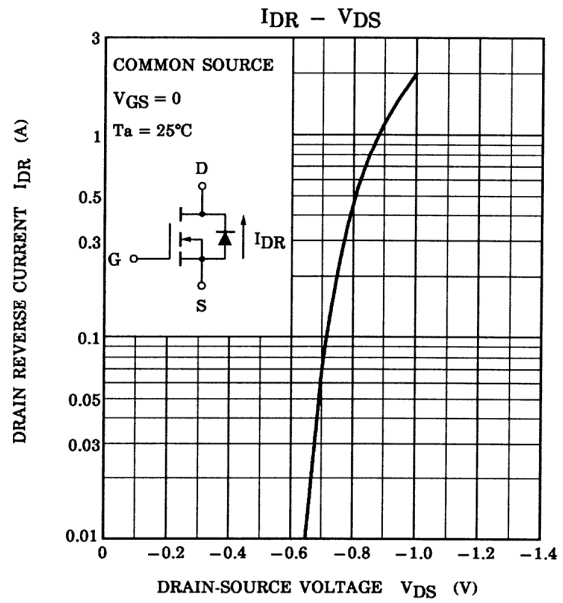
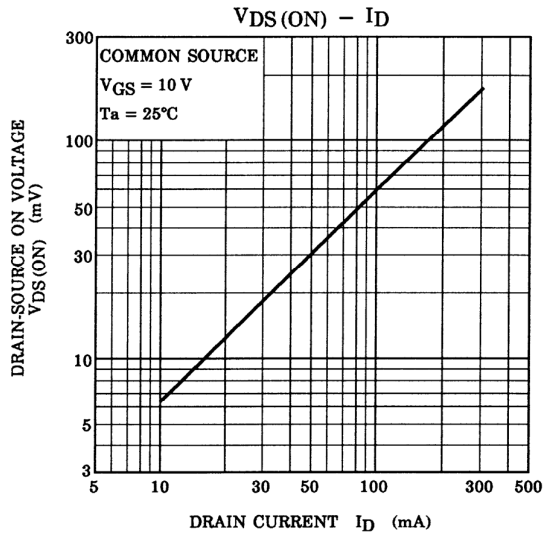
Weight: 0.13 g (typ.)

Electrical Characteristics (Ta = 25°C)

| Characteristics | | Symbol | Test Condition | Min | Typ. | Max | Unit |
|--------------------------------|---------------|---------------|--|-----|------|-----------|---------------|
| Gate leakage current | | I_{GSS} | $V_{GS} = \pm 10\text{ V}, V_{DS} = 0$ | — | — | ± 100 | nA |
| Drain cut-off current | | I_{DSS} | $V_{DS} = 60\text{ V}, V_{GS} = 0$ | — | — | 10 | μA |
| Drain-source breakdown voltage | | $V_{(BR)DSS}$ | $I_D = 1\text{ mA}, V_{GS} = 0$ | 60 | — | — | V |
| Gate threshold voltage | | V_{th} | $V_{DS} = 10\text{ V}, I_D = 1\text{ mA}$ | 2 | — | 3.5 | V |
| Forward transfer admittance | | $ Y_{fs} $ | $V_{DS} = 10\text{ V}, I_D = 50\text{ mA}$ | 100 | — | — | mS |
| Drain-source ON resistance | | $R_{DS(ON)}$ | $I_D = 50\text{ mA}, V_{GS} = 10\text{ V}$ | — | 0.6 | 1.0 | Ω |
| Drain-source ON voltage | | $V_{DS(ON)}$ | $I_D = 50\text{ mA}, V_{GS} = 10\text{ V}$ | — | 30 | 50 | mV |
| Input capacitance | | C_{iss} | $V_{DS} = 10\text{ V}, V_{GS} = 0, f = 1\text{ MHz}$ | — | 55 | 65 | pF |
| Reverse transfer capacitance | | C_{rss} | | — | 13 | 18 | pF |
| Output capacitance | | C_{oss} | | — | 40 | 50 | pF |
| Switching time | Rise time | t_r |  <p>D.U. $\leq 1\%$ V_{IN}: $t_r, t_f < 5\text{ ns}$ $(Z_{out} = 50\ \Omega)$</p> | — | 8 | — | ns |
| | Turn-on time | t_{on} | | — | 14 | — | |
| | Fall time | t_f | | — | 35 | — | |
| | Turn-off Time | t_{off} | | — | 75 | — | |

Note: This transistor is the electrostatic sensitive device. Please handle with caution.





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20070701-EN GENERAL

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